

Dry Etch Test, CSAR, performed by Tine Greibe, Nov-Jan 2014-2015		
	Wafer 3.07	Wafer 6.05
Spin Coat	AR-P 6200, 4000 rpm, softbaked 60s @ 150°C, 182 nm thickness (ellipsometry) May-2014	AR-P 6200, 2000 rpm, softbaked 120s @ 150°C, 248 nm thickness (ellipsometry) August-2014
Dry Etch	75 s total (3 runs) Main pressure 3-5 mTorr 34 sccm BCl <sub>3</sub> , 6 sccm Cl <sub>2</sub> Various Platen temperatures (-15 °C → 20 °C) Etch rate in CSAR 100-160 nm/min November-2014	3:20 min Bosch process, C4F8/SF <sub>6</sub> , 0:30 min continuous process, C4F8/SF <sub>6</sub> Platen temperature 10 °C Etch rates in CSAR: ~13 nm/min (Bosch), ~90 nm/min (cont.) November-2014
Removal	AR-600-71, room temperature, rinsed in IPA, N <sub>2</sub> dried, January 2015	

